

N-Channel Enhancement Mode Power MOSFET

Description

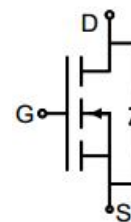
The GT035N12T uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

- V_{DS} 120V
- I_D (at $V_{GS} = 10V$) 180A
- $R_{DS(ON)}$ (at $V_{GS} = 10V$) < 3.8m Ω
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters



Schematic diagram



TO-220

Ordering Information

Device	Package	Marking	Packaging
GT035N12T	TO-220	GT035N12	50pcs/Tube

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	120	V
Continuous Drain Current	I_D	180	A
		114	
Pulsed Drain Current (note1)	I_{DM}	720	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	P_D	230	W
Single pulse avalanche energy (note2)	E_{AS}	529	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	50	$^\circ\text{C/W}$
Maximum Junction-to-Case	R_{thJC}	0.54	$^\circ\text{C/W}$

Specifications T _J = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	120	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 120V, V _{GS} = 0V	--	--	1	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2.0	3.0	4.0	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 50A	--	3.1	3.8	mΩ
Forward Transconductance	g _{FS}	V _{GS} = 5V, I _D = 50A	--	55	--	S
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 60V, f = 0.5MHz	--	8335	--	pF
Output Capacitance	C _{oss}		--	860	--	
Reverse Transfer Capacitance	C _{rss}		--	7	--	
Total Gate Charge	Q _g	V _{DD} = 60V, I _D = 50A, V _{GS} = 10V	--	126	--	nC
Gate-Source Charge	Q _{gs}		--	38	--	
Gate-Drain Charge	Q _{gd}		--	31	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 60V, I _D = 50A, R _G = 4.7Ω	--	26	--	ns
Turn-on Rise Time	t _r		--	84	--	
Turn-off Delay Time	t _{d(off)}		--	54	--	
Turn-off Fall Time	t _f		--	18	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25°C	--	--	180	A
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 50A, V _{GS} = 0V	--	--	1.2	V
Reverse Recovery Charge	Q _{rr}	I _F = 50A, V _{GS} = 0V di/dt=100A/us	--	176	--	nC
Reverse Recovery Time	T _{rr}		--	79	--	ns

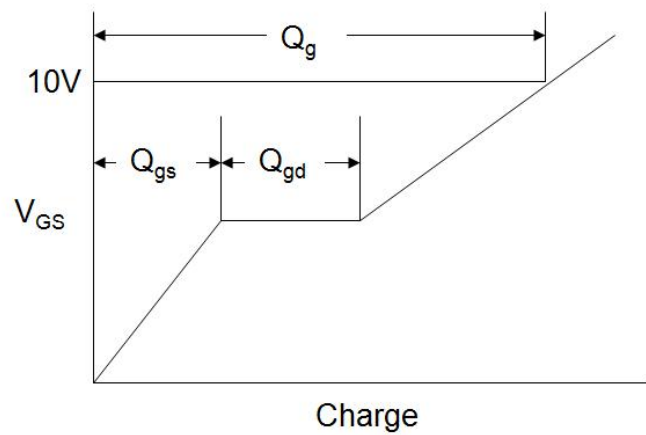
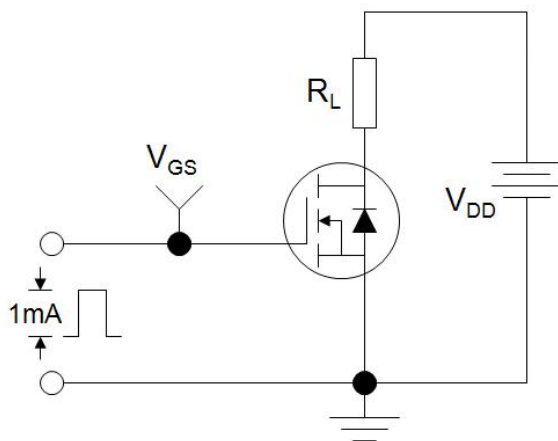
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition : $T_J = 25^{\circ}\text{C}, V_{DD} = 50V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$

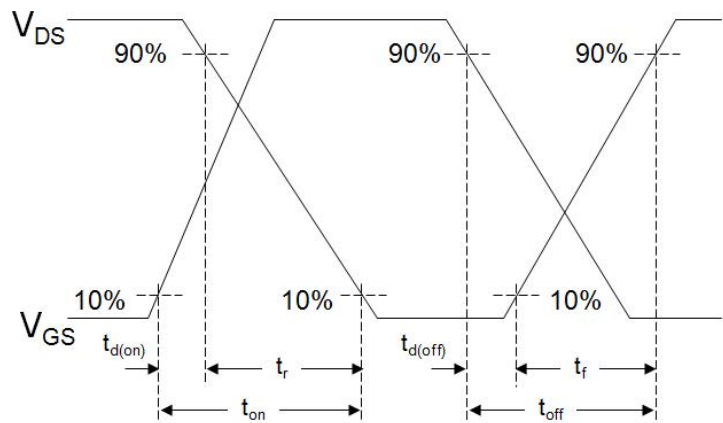
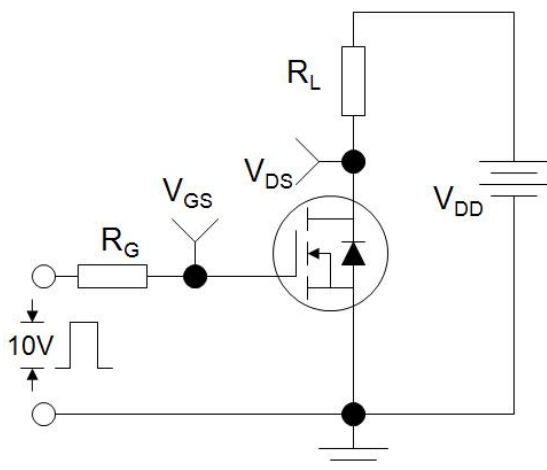
The table shows the minimum avalanche energy, which is 1444mJ when the device is tested until failure

3. Identical low side and high side switch with identical R_G

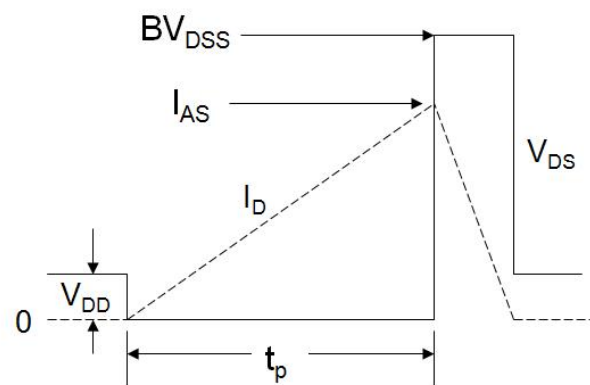
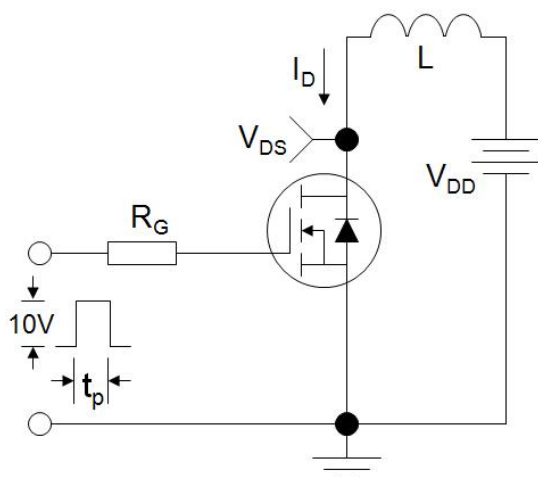
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

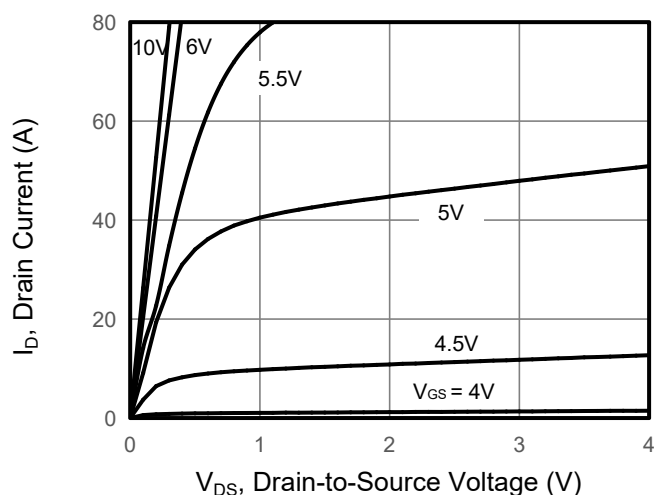


Figure 2. Transfer Characteristics

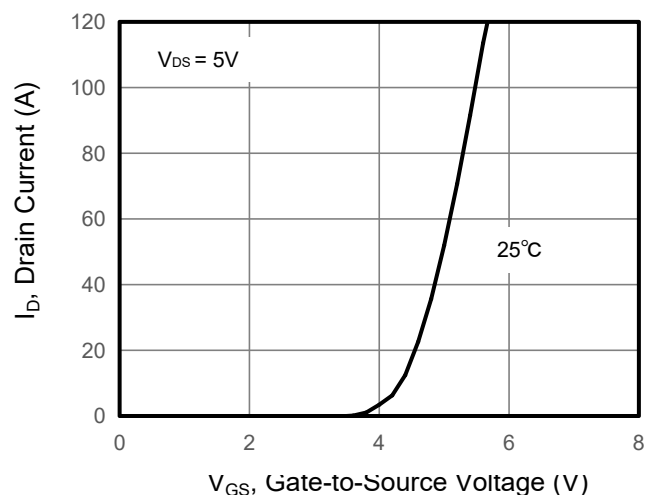


Figure 3. Drain Source On Resistance

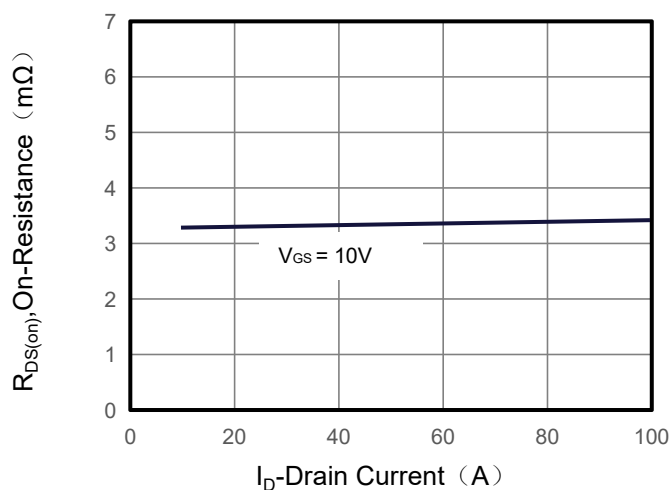


Figure 4. Gate Charge

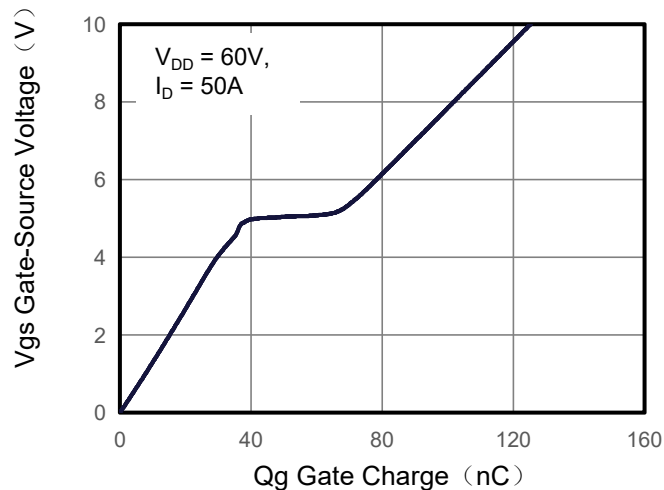


Figure 5. Capacitance

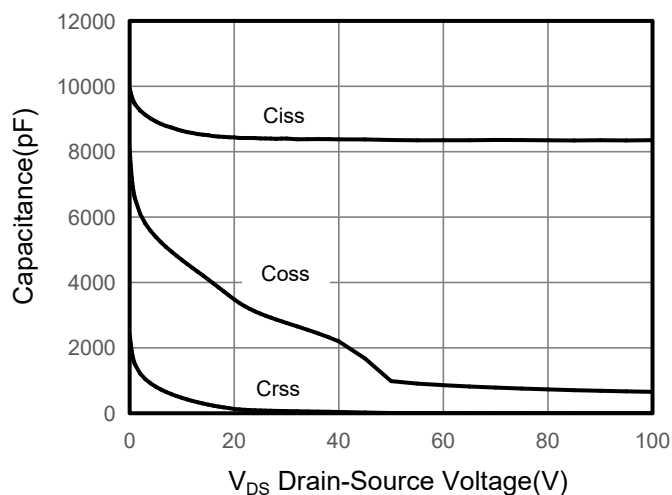
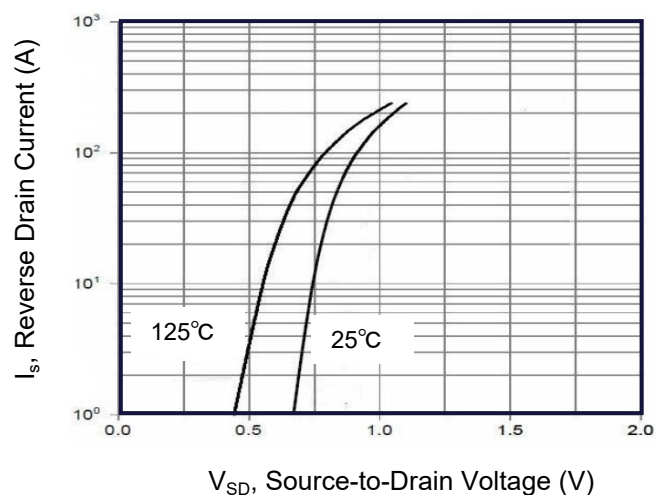


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

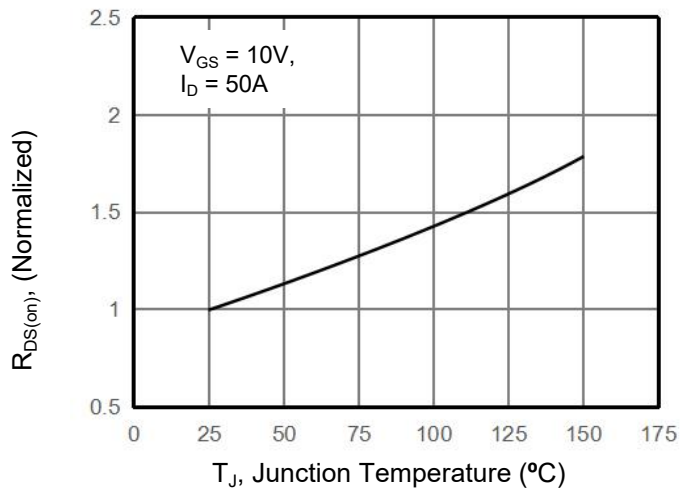


Figure 8. Safe Operation Area

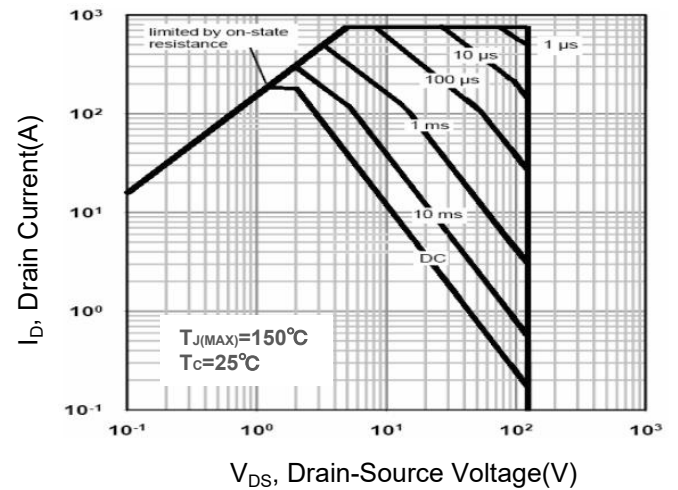


Figure 9. Maximum Continuous Drain Current vs Case Temperature

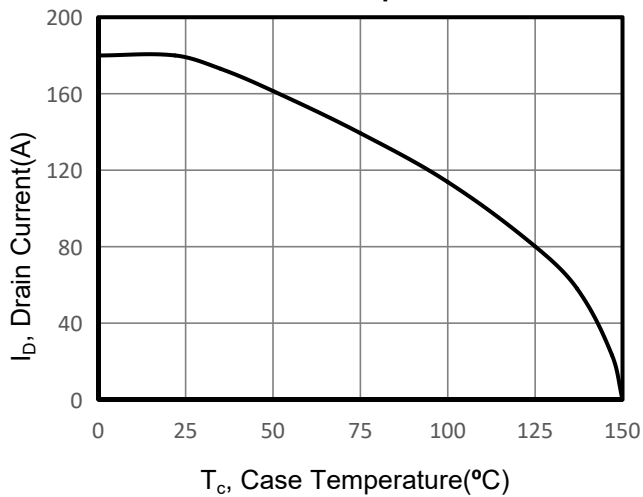
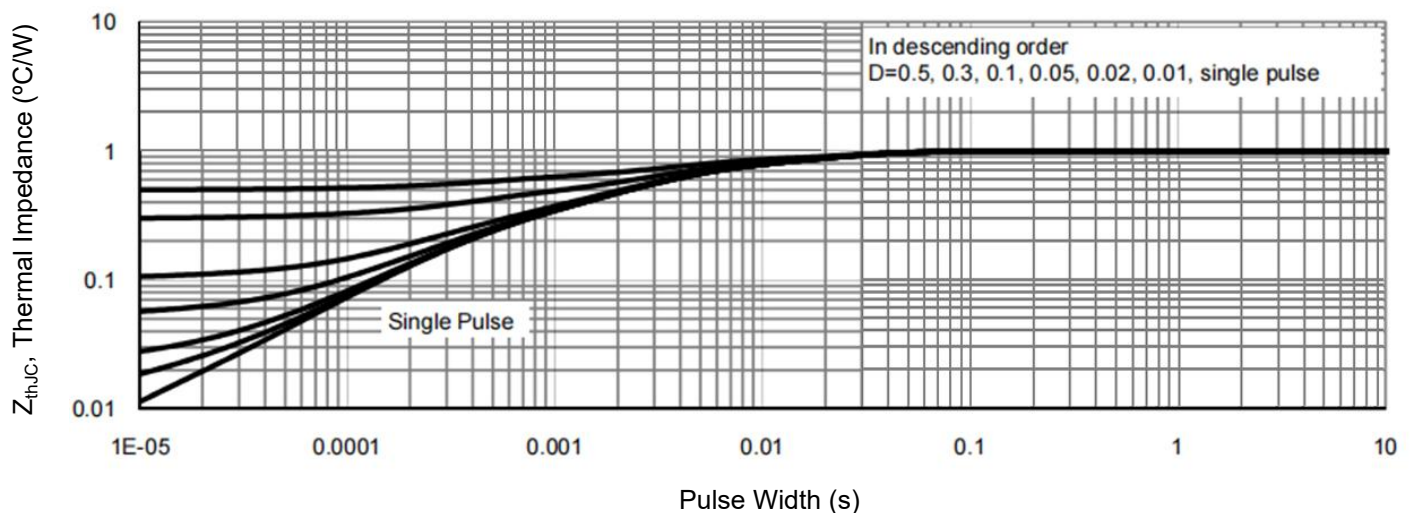
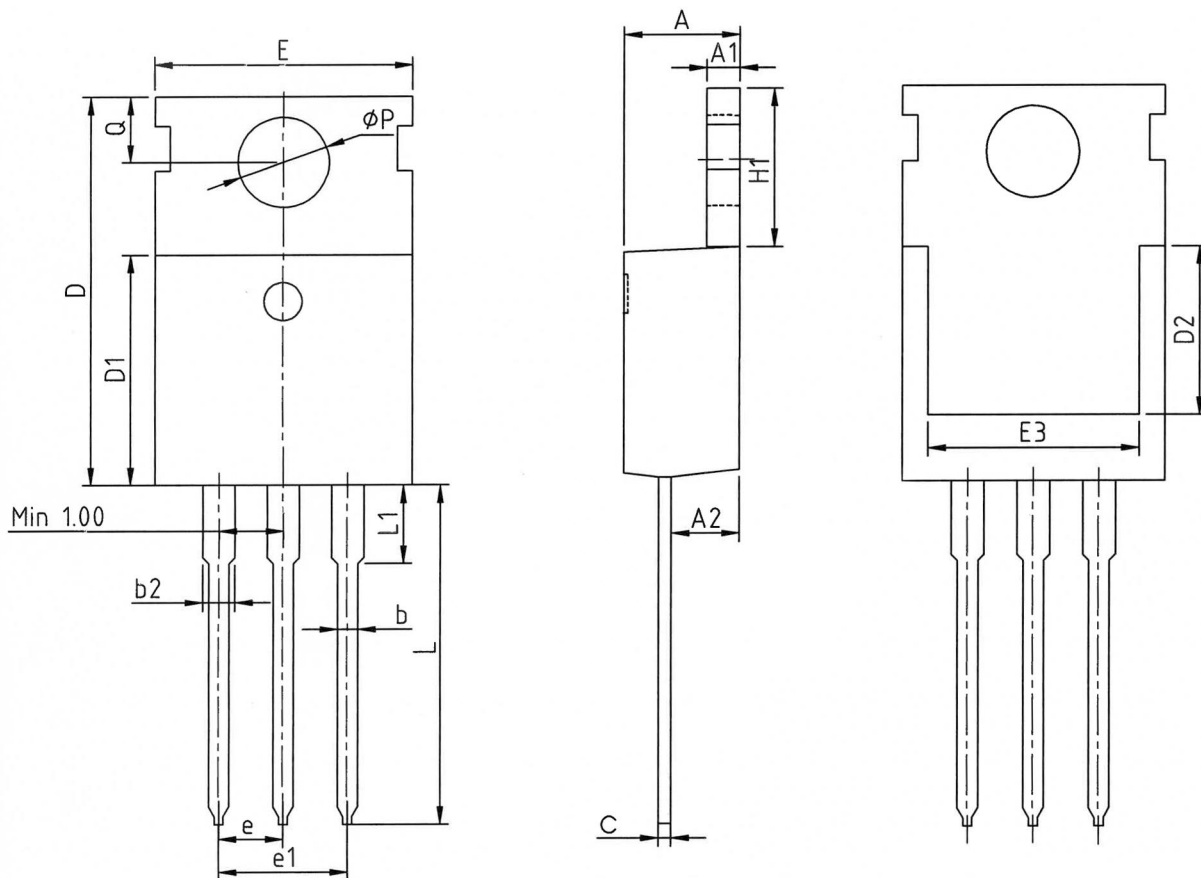


Figure 10. Normalized Maximum Transient Thermal Impedance



TO-220 Package Information



COMMON DIMENSIONS

SYMBOL	MIN	NOM	MAX
A	4.37	4.57	4.70
A1	1.25	1.30	1.40
A2	2.20	2.40	2.60
b	0.70	0.80	0.95
b2	1.17	1.27	1.47
c	0.45	0.50	0.60
D	15.10	15.60	16.10
D1	8.80	9.10	9.40
D2	5.50	6.30	7.10
E	9.70	10.00	10.30
E3	7.00	7.80	8.60
e	2.54 BSC		
e1	5.08 BSC		
H1	6.25	6.50	6.85
L	12.75	13.50	13.80
L1	-	3.10	3.40
ΦP	3.40	3.60	3.80
Q	2.60	2.80	3.00